d-cell Ising model Note

Roger Luo

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Residual entropy is defined as logrithm of ground state degeneracy. Thus if the ground state has a large degeneracy that is extensive, then we will have an extensive residual entropy. The hamiltonian of our concern is defined as following

$$H_p = \sum_{c_{p+1}} \prod_{i \in c_{p+1}} \sigma_i$$

in our case, this Hamiltonian is defined on a d-dimensional hypercubic lattice, where $d \ge p$, where c_p is a p-cell, we will discuss the formal definition of a cell later (it is not needed to understand the physics setup). Here for example 0-cell is a vertice, 1-cell is an edge, and 2-cell is a plaquette, and so on. The element of a p-cell is all (p-1)-cell that constructs the p-cell, thus for H_0 , we have c_1 , thus we have sites on each vertices and the Hamiltonian writes as a standard Ising model with nearest-neighbor interaction,

$$H_0 = \sum_{\langle i,j \rangle} \sigma_i \sigma_j$$

and for p = 1, we have spins on the edges

$$H_1 = \sum_{\square} \sigma_1 \sigma_2 \sigma_3 \sigma_4$$

for p = 2, we have spins on the faces

$$H_2 = \sum_{\Box \in \text{faces of the hypercube}} \sigma_1 \sigma_2 \sigma_3 \sigma_4 \sigma_5 \sigma_6$$

The ground state degeneracy is mainly due to the gauge invariance, for example, for p=1, d=2, in a plaquette one can exchange the spin on two edges attached to the same vertex without changing the energy of our plaquette. So we can let each vertices have a spin -1,1 to represent the spin on two edges attached to it as showed in Figure 1. No matter how one changes the spin on the edges, the product of edge spins that attached to the same vertex on the vertices is the same. This also means there is an effective spin at the vertex (denotes whether all edges attached to the vertex) is completely free. Thus it creates a freedom of N_0 spins where N_0 is the number of 0-cell (the vertices), thus the degeneracy is at scale 2^{N_0} .

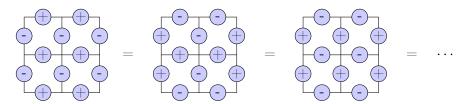


Figure 1: gauge freedom in the 2-cell case (plaquette), H_1 is the same for these configurations. 2nd configuration is obtained by flipping all spins attached to center vertex, 3rd configuration is obtained by flipping all spins attached all vertices.

Similarly, if p = 2, d = 3, on the faces of a cube, the 4 faces attached to the same edge can flip their spins. Thus we have a free spin on each edge of number N_1 . However, this over-counts because

when flipping all the effective spin on the edges that attached to the same vertex corresponding to the same face spins. Thus the total number of free spins should be $N_1 - N_0$.

Thus following this derivation, and generalize the above conclusion. We know, the free spins at p-cell is flipping all spins of p-cell that attached to p-1-cell, and the free spins for general p can be obtained by counting the free spins of p-1 case. Thus we have

$$N_{free} = N_{p-1} - (N_{p-2} - (N_{p-3} - \dots (N_1 - N_0)))$$

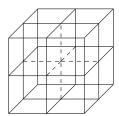
= $N_{p-1} - N_{p-2} + N_{p-3} - \dots N_1 \pm N_0$

thus the ground state degeneracy is $2^{N_{p-1}-N_{p-2}+N_{p-3}-\cdots N_1\pm N_0}$ for hypercubic lattice with no defects (the defects will create an O(1) correction to the degeneracy).

This gives the residual entropy of the ground state,

$$S/N = \frac{N_{p-1} - N_{p-2} + N_{p-3} - \dots + N_1 \pm N_0}{N_0} log(2)$$

for p = 2, d = 3 case, we have $N_1 = 3N_0$, thus S/N = 2log(2)



However, the above derivation can be much simpler, which is two sentence in the original self-correcting memory paper[2]. It is actually the Euler characteristic of the cell chain complex. Or the Betti number as the rank of the *n*-th singular homology group[3, 1].

References

- [1] Benjamin Young Denis Sjerve. Algebra toplogy, page 39.
- [2] Matthew B Hastings, Grant H Watson, and Roger G Melko. Self-correcting quantum memories beyond the percolation threshold. *Physical review letters*, 112(7):070501, 2014.
- [3] Wiki. Euler characteristic.